



Super-ALPIDE: Development of Electromechanical Integration Demonstrators for the ALICE ITS3

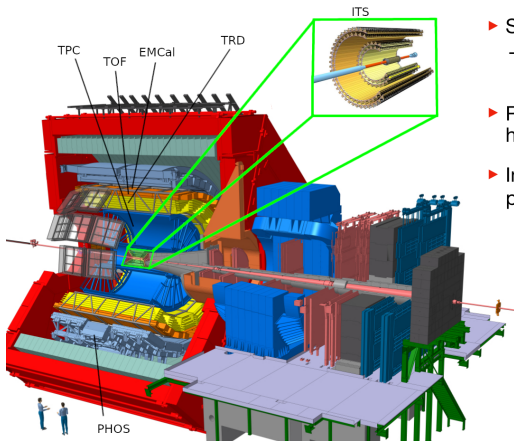
Alperen YÜNCÜ

July 27, 2022

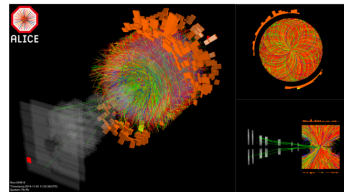


FSP ALICE
Erforschung von
Universum und Materie

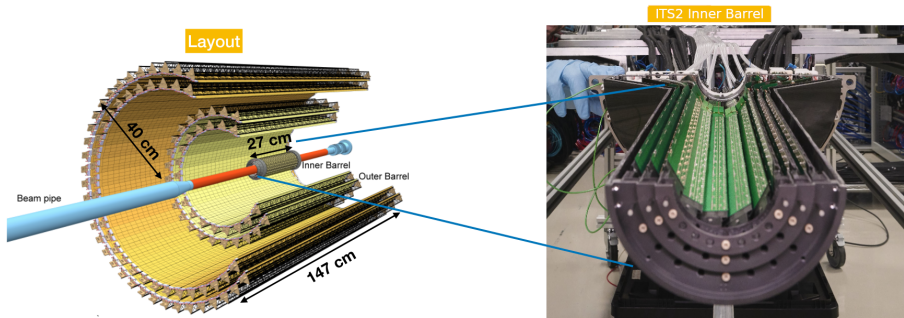
Detector and main goals



- ▶ Study of QGP in heavy-ion collisions at LHC
- i.e. up to $O(10k)$ particles to be tracked in a single event
- ▶ Reconstruction of charm and beauty hadrons
- ▶ Interest in low momentum (≤ 1 GeV/c) particle reconstruction

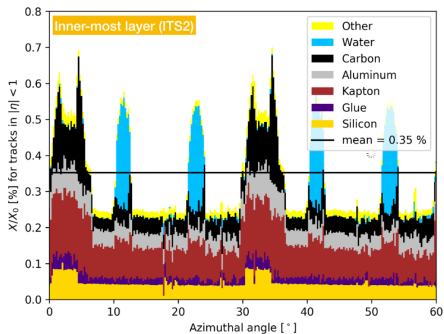


Current Inner Tracking System (ITS2)



- ITS2 is expected to perform according to specifications or even better
- The inner barrel is ultra-light ($0.35\% X_0$ per layer) but still most of the material comes from supports \implies **further improvements seem possible**
- Key questions:
 - ▶ Can we get closer to the interaction point?
 - ▶ Can we reduce the material budget even further?

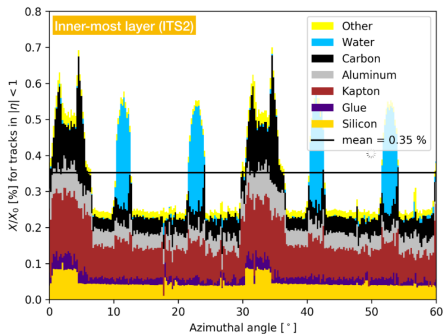
Motivation for ITS3



- Observations:

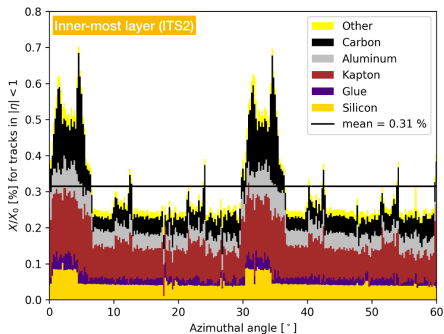
- ▶ 0.35 % X_0 per layer
- ▶ Si makes only 1/7th of total material
- ▶ Irregularities due to support/cooling

Motivation for ITS3



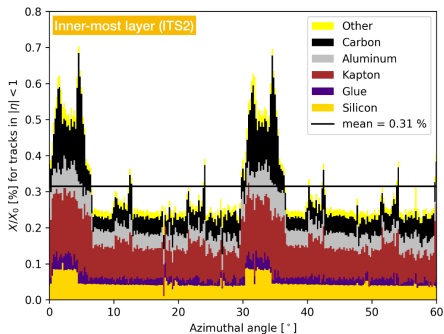
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 - ▶ Possible if power consumption stays below 20 mW/cm^2
 - ▶ Air cooling

Motivation for ITS3



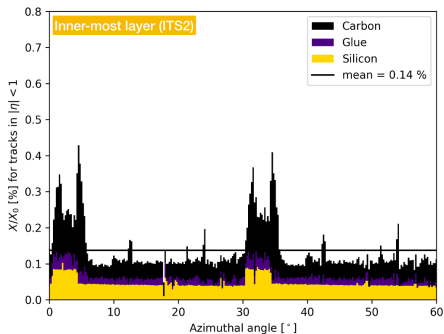
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Motivation for ITS3



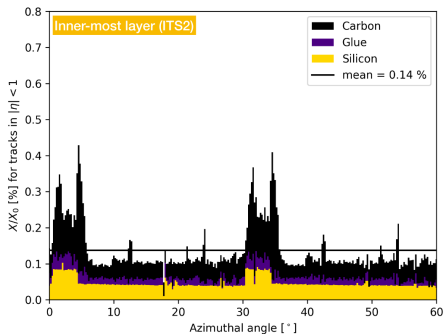
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- Removal of the circuit boards (power+data)
 - ▶ Possible if integrated on chip

Motivation for ITS3



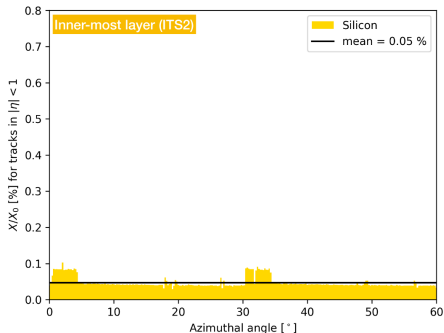
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Motivation for ITS3



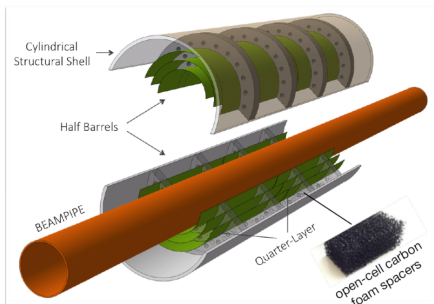
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- Removal of mechanical support
 - ▶ Benefit from increased stiffness by bending Si wafers into cylindrical shape

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- Removal of mechanical support
 - ▶ Benefit from increased stiffness by bending Si wafers into cylindrical shape
 - ▶ 0.05 % X_0 per layer

ITS3 detector concept

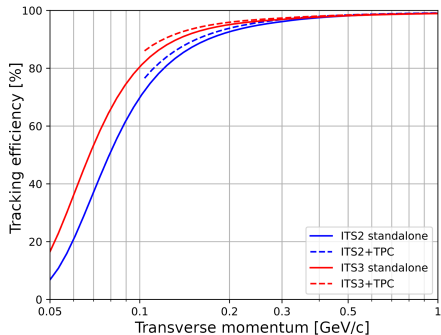
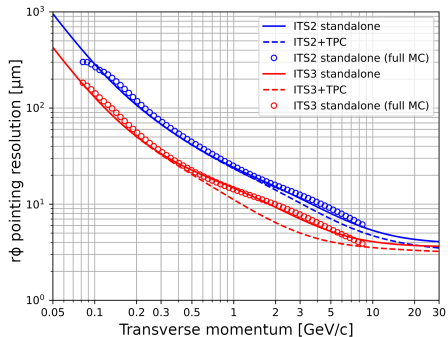


Beam pipe Inner/Outer Radius (mm)	16.0/16.5		
IB Layer Parameters	Layer 0	Layer 1	Layer 2
Radial position (mm)	18.0	24.0	30.0
Length (sensitive area) (mm)	280		
Pseudo-rapidity coverage	± 2.5	± 2.3	± 2.0
Active area (cm ²)	610	816	1016
Pixel sensor dimensions (mm ²)	280 x 56.5	280 x 75.5	280 x 94
Number of sensors per layer	2		
Pixel size (μm^2)	O (10 x 10)		

- Key ingredients:
 - ▶ 280 mm wafer-scale sensors, fabricated using **stitching** (Tower Partners Semiconductor (TPSCo) 65 nm CMOS Imaging Sensor (CIS) process)
 - ▶ Thinned down to 20-40 μm (0.02-0.04% X_0), making them **flexible**
 - ▶ Bent to the target radii
 - ▶ Mechanically held in place by **carbon foam ribs**
- Key benefits:
 - ▶ Extremely low material budget: 0.02-0.04% X_0 (beampipe: 500 μm Be: 0.14% X_0)
 - ▶ Homogeneous material distribution: negligible systematic error from material distribution

THE WHOLE DETECTOR WILL COMPRISE SIX (!) SENSORS (CURRENT ITS IB: 432) AND BARELY ANYTHING ELSE

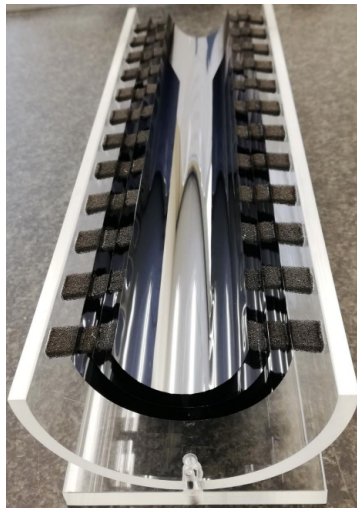
ITS3 performance



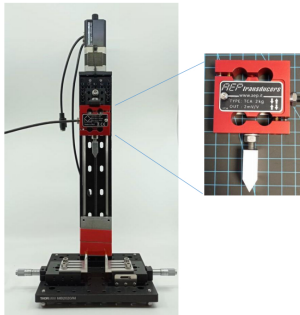
- Improvement on pointing resolution is **factor of 2** over all momenta.
- Large improvement on tracking efficiency especially for low momenta.

- Questions:

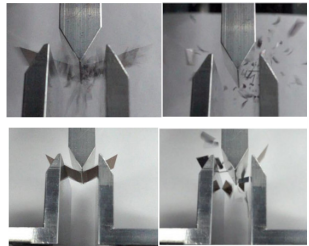
- ▶ Can silicon be bent without breaking?
- ▶ Are ASICs still functional in bent chip?
- ▶ Can wafer-scale, thinned sensors be integrated **without** additional support structure?
- ▶ Can 280 mm long silicon sensor be produced?



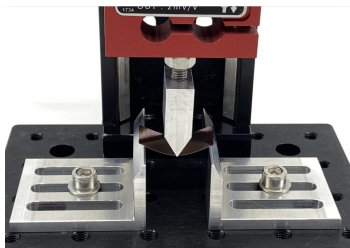
Bending Test



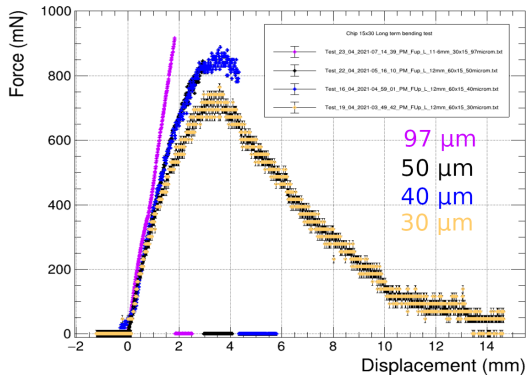
- Bending modulus
- Elastic - plastic region
- Breaking point
- Minimum radius



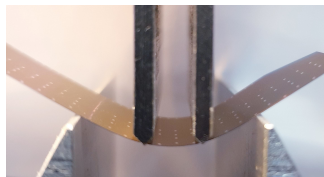
Bending Test (3-point test)



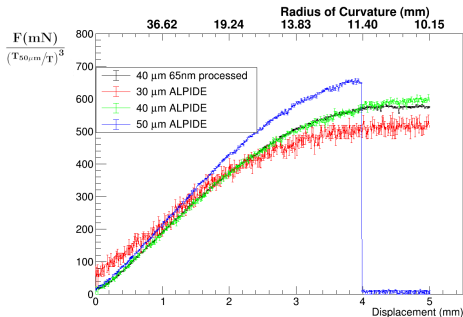
ALICE ITS3 Bending test



Bending Test (4-point test)



- Monolithic Active Pixel Sensors are quite flexible
 - ▶ already at thicknesses that are used for current detectors
- Bending force scales as $(\text{thickness})^{-3}$
 - ▶ large benefit from thinner sensors
- Breakage at smaller radii for thinner chips
 - ▶ again benefit from thinner sensors



ITS3 TARGET RADIUS AND THICKNESS ARE VERY FEASIBLE

bent ALPIDE

doi.org/10.1016/j.nima.2021.166280

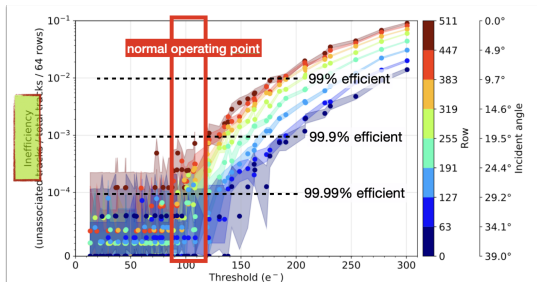
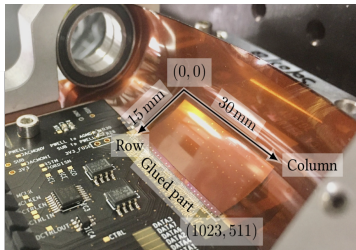
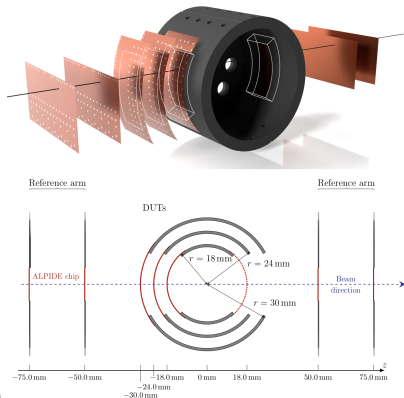
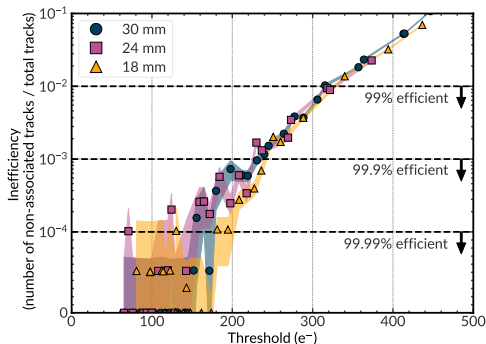


Fig. 10: Inefficiency as a function of threshold for different rows and incident angles with partially logarithmic scale (10⁻¹ to 10⁻⁵) to show fully efficient rows. Each data point corresponds to at least 8k tracks.



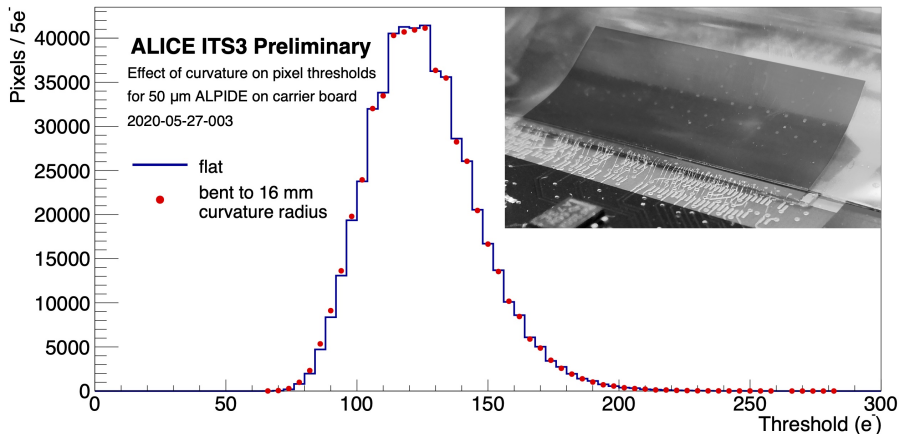
- Bent ALPIDE has **high efficiency**
- ASICs are functional in bent ALPIDE

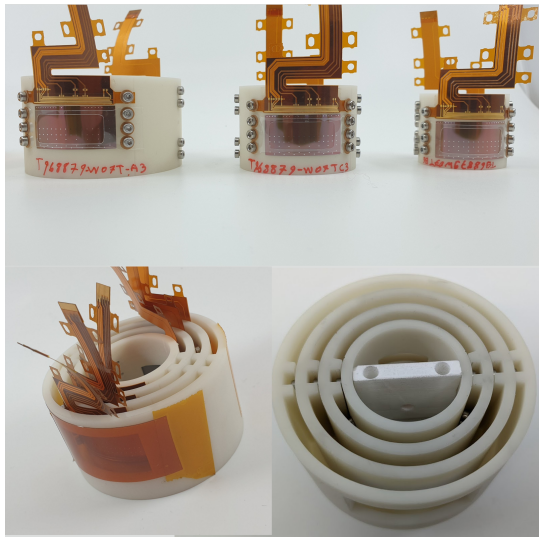
bent ALPIDE



- Still has high efficiency on target radii

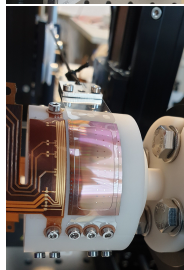
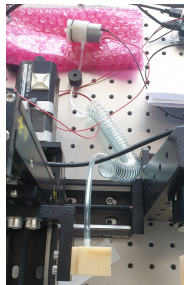
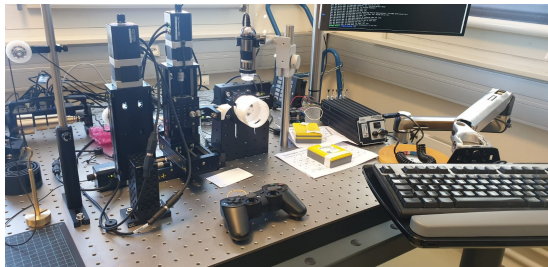
Chip bending performance



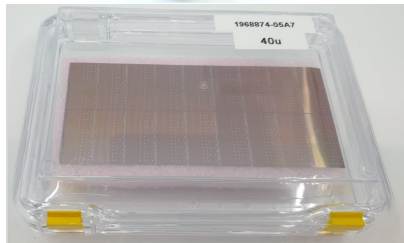
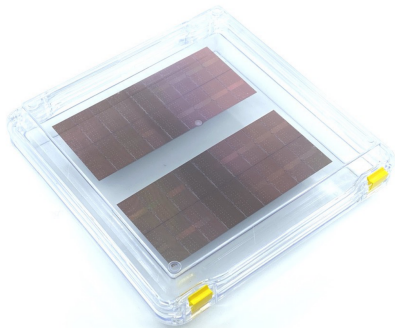


- μ ITS3 a mock-up of final ITS3
 - ▶ 6 ALPIDE bent to ITS3 target radii
 - ▶ Experience with handling thin, bent silicon was gained
- Also used with Cu target in the center, expect to see 120 GeV p-Cu collisions
- Analysis of μ ITS3 is in progress.

μ ITS Preperation Setup

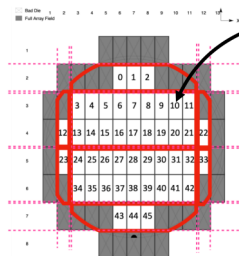


Super ALPIDE

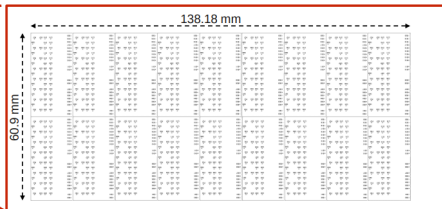


- To study the **bending** and **interconnection** of large pieces of processed chips, "super-ALPIDE" is built.
- Comprises of **1 silicon piece cut** from an ALPIDE wafer size of 14 cm × 6 cm

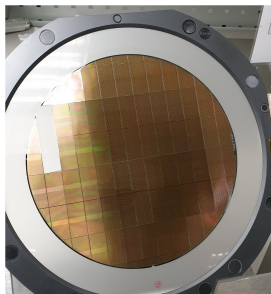
Super ALPIDE



ALPIDE chips

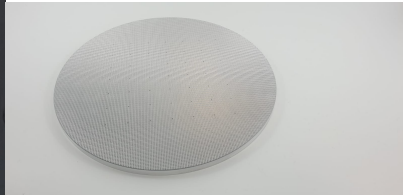
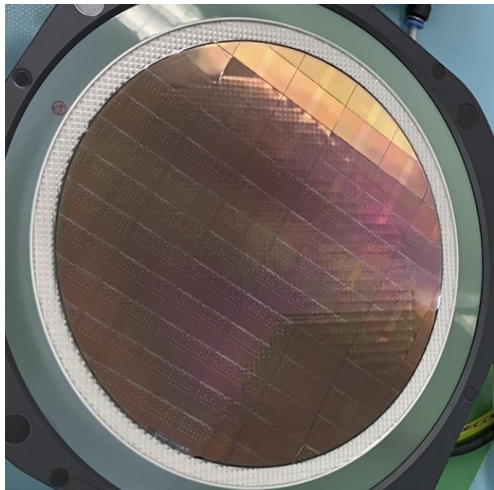


18 ALPIDE chips, covering about a half of an ITS3 half-Layer0

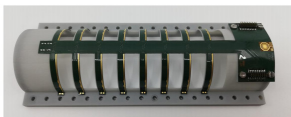
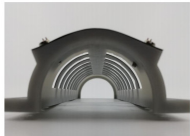
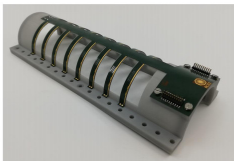
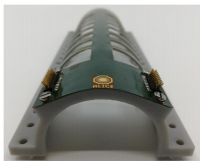


- Super-ALPIDEs are actually an array of ALPIDEs.
- They consist 9×2 ALPIDE chips.

Picking up Super ALPIDE Chips

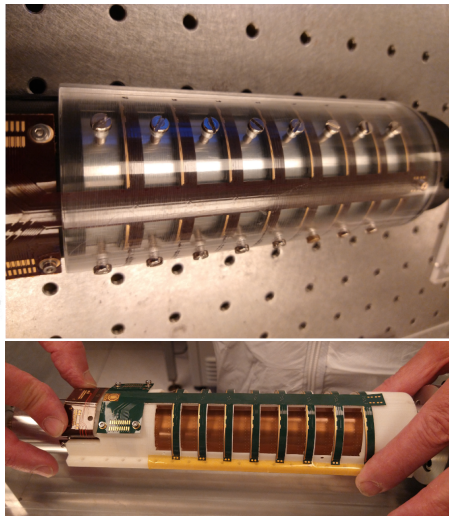
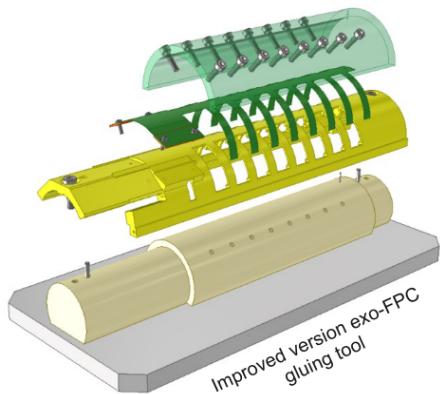


- Tested different methods how to pick large and very thinned chips
- Die-ejector with fine grid is quite efficient.



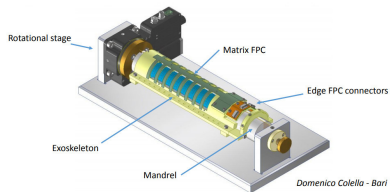
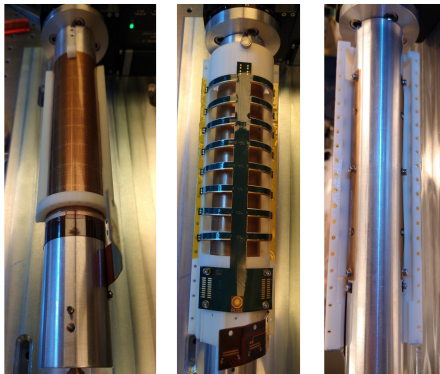
- 3-D printed.
- Designed to support super-ALPIDEs after bending.
- Windows to reach interconnection points at middle of super-ALPIDE
- FPC glued for connections

Gluing FPC



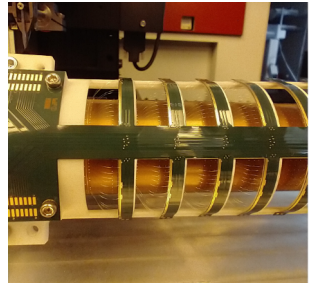
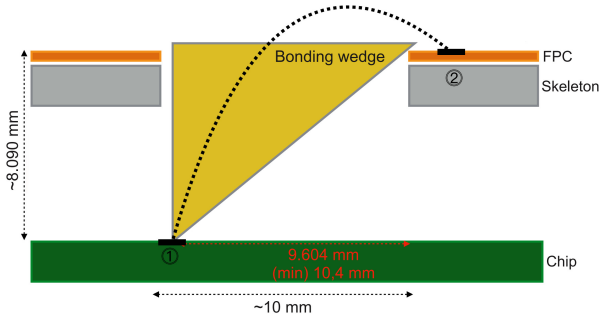
Bending Super ALPIDEs

Super-ALPIDE wire-bonding setup



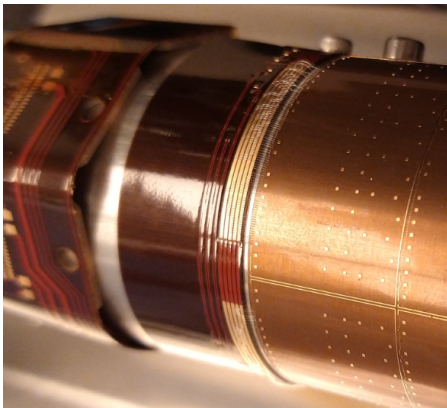
- Super ALPIDE is being rolled on mandrel
- Longerons are placed gently
- Exoskeleton is placed on top of the Super APIDE
- prepare for bonding

Bonding



- The most of the ALPIDEs will be bonded to FPC on Exoskeleton via long wires

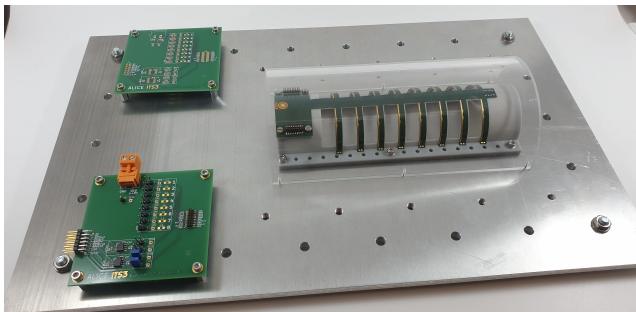
Bonding



- The **first row of ALPIDEs** will be wire-bonded to an edge-FPC (just like final **ITS3**)
- The rest will be bonded to FPC on **exoskeleton** via long wires



Super ALPIDE Test Setup

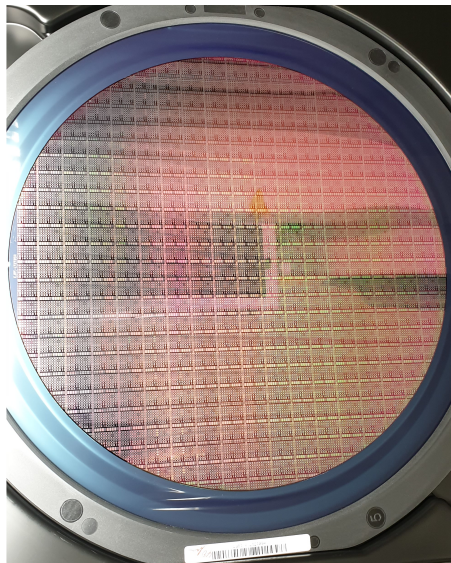


- Bonding and assembly of super ALPIDE is still ongoing at Bari.
- Meanwhile, Front-end readout circuitry is being built at CERN
- Test setup is ready.
- Tests of Super-ALPIDEs will start in November

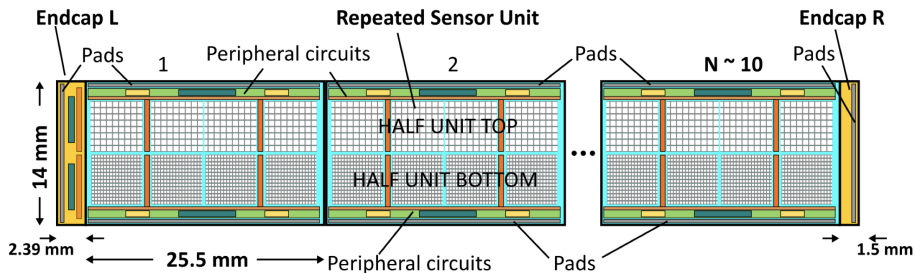
MLR1 Chips picking



- For **MLR1 chips on 12-inch wafers**, Die Ejector didn't help to remove chip
- After some number of methods failed we ask the prudocion company change the tape they use
- New blue tape is much **less adhesive** and MLR1 chips easily can be removed by die ejector.



Stitching



- Stitching used to connect metal traces for **power distribution** and **long range on-chip interconnect busses** for control and data readout
- **Primary goals:**
 - ▶ Learn **stitching** to make a charged-particle detector
 - ▶ **Interconnect** power and signals on wafer scale design
 - ▶ Learn about **yield**
 - ▶ Study power, leakage, spread, noise, speed



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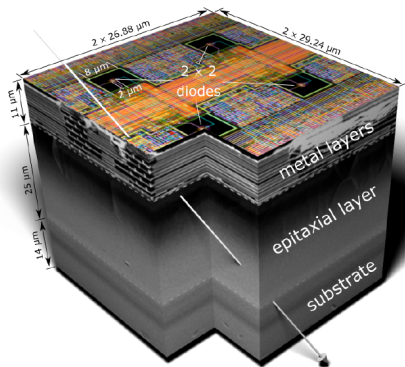
Summary

- Silicon is **flexible** enough to achieve targeted radii
- There is almost **no efficiency loss** at ASIC on bent chips
- Thanks to **Super-ALPIDE** study we have the know-how about how to deal with large and thin chips
- Almost ready for the production of the first prototypes of **wafer-scale chips**

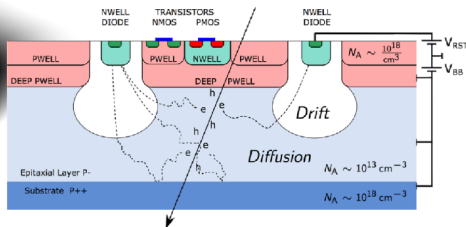
THANK YOU

BACKUP

ALPIDE Technology

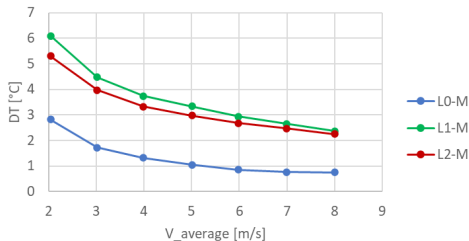


- ▶ **Process:** TowerJazz 180 nm CIS
 - deep p-well to allow CMOS circuitry inside matrix
 - reverse-substrate bias
- ▶ **Detection layer:** 25 μm high-resistive ($>1\text{k}\Omega\text{cm}$) epitaxial layer
- ▶ **Thickness:** 100 μm (OB) or 50 μm (IB)

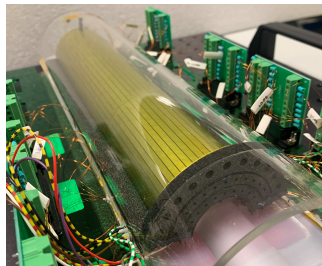
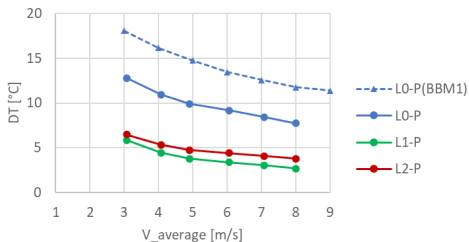


Wind Tunnel Cooling Studies

Matrix 20 mW/cm²



Periphery 900 mW/cm²



- Different **power & air speed**
- Carbon foam radiator are key for heat removal at periphery
 - ▶ L1 and L2 DT < 10°C
 - ▶ L0 has relatively larger temperature DT to air (further optimization on L0 Carbon foam layout)
 - ▶ Power density concentrated on **2.5 mm periphery**